

45V NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

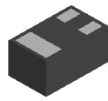
Features

- Epitaxial Die Construction
- Ultra-Small Leadless Surface Mount Package
- Ultra Low Profile (0.4mm max)
- Complementary PNP Type Available (BC857BLP4)
- **"Lead Free", RoHS Compliant (Note 1)**
- **Halogen and Antimony Free "Green" Device (Note 2)**

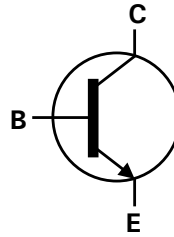
Mechanical Data

- Case: DFN1006H4-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0008 grams (approximate)

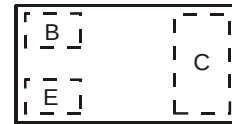
DFN1006H4-3



Bottom View



Device Symbol



Top View
Device Schematic

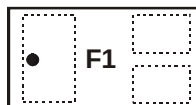
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BC847BLP4-7	F1	7	8mm	3,000
BC847BLP4-7B	F1	7	8mm	10,000

- Notes:
1. No purposefully added lead.
 2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

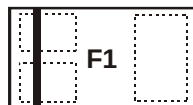
Marking Information

BC847BLP4-7



Top View
Dot Denotes
Collector Side

BC847BLP4-7B



Top View
Bar Denotes Base
and Emitter Side

F1 = Product Type Marking Code

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	I _C	100	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	250	mW
Thermal Resistance, Junction to Ambient (Note 4)	R _{θJA}	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic (Note 5)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	—	—	V	I _C = 10μA, I _B = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	—	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6	—	—	V	I _E = 1μA, I _C = 0
DC Current Gain	h _{FE}	200	350	450	—	V _{CE} = 5.0V, I _C = 2.0mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	80 200	250 600	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	700 900	—	mV	I _C = 10mA, I _B = 0.5mA I _C = 100mA, I _B = 5.0mA
Base-Emitter Voltage	V _{BE(on)}	580 —	640 725	700 770	mV	V _{CE} = 5.0V, I _C = 2.0mA V _{CE} = 5.0V, I _C = 10mA
Collector-Cutoff Current	I _{CBO}	— —	— —	15 5.0	nA μA	V _{CB} = 30V V _{CB} = 30V, T _A = 150°C
Gain Bandwidth Product	f _T	100	—	—	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Collector-Base Capacitance	C _{CBO}	—	3.0	—	pF	V _{CB} = 10V, f = 1.0MHz

Notes: 4. Device mounted on FR-4 PCB.
5. Short duration pulse test used to minimize self-heating effect.

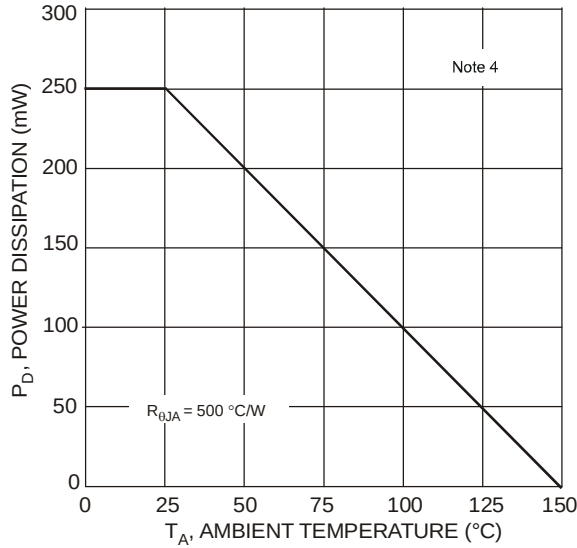


Fig. 1 Power Derating Curve

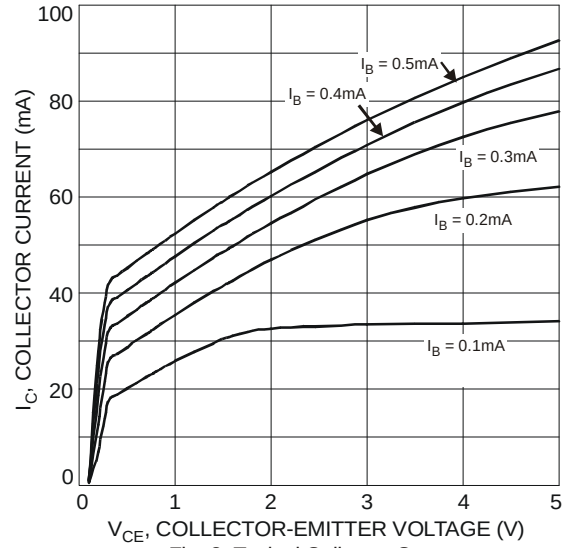


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

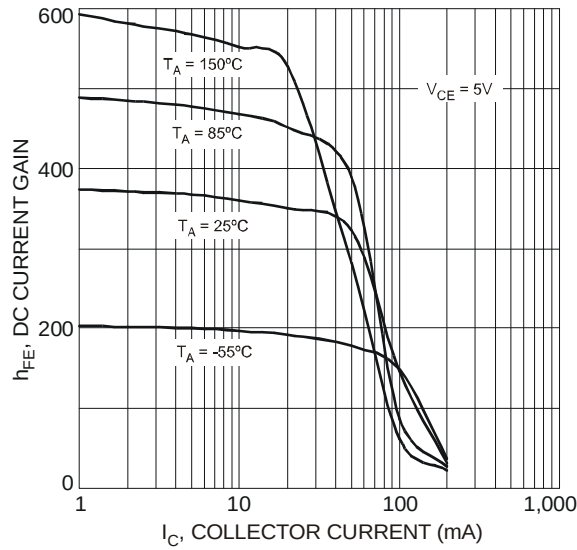


Fig. 3 Typical DC Current Gain vs. Collector Current

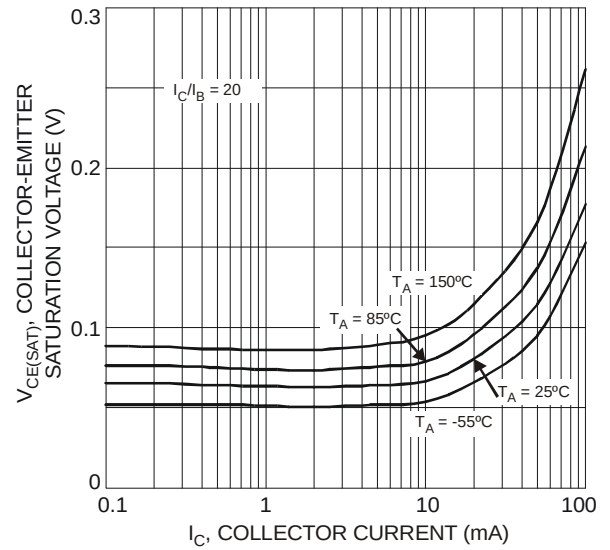


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

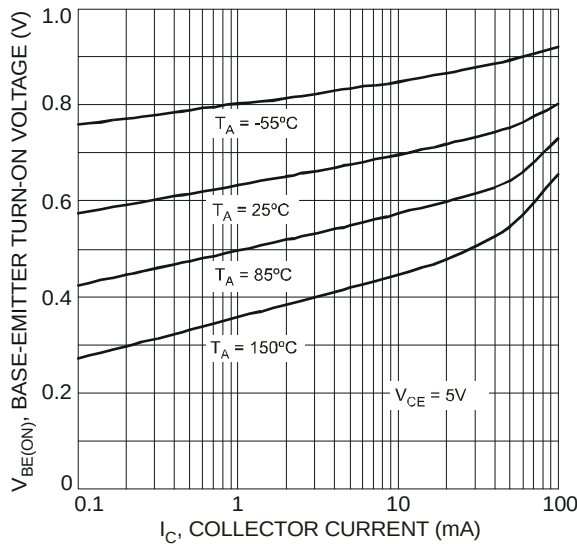


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

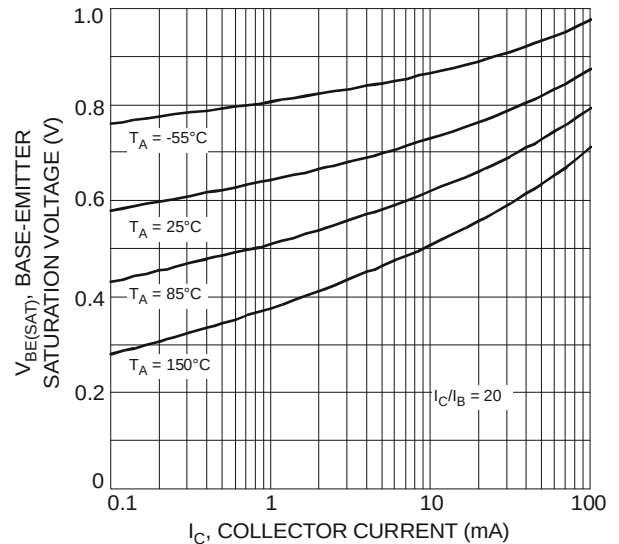
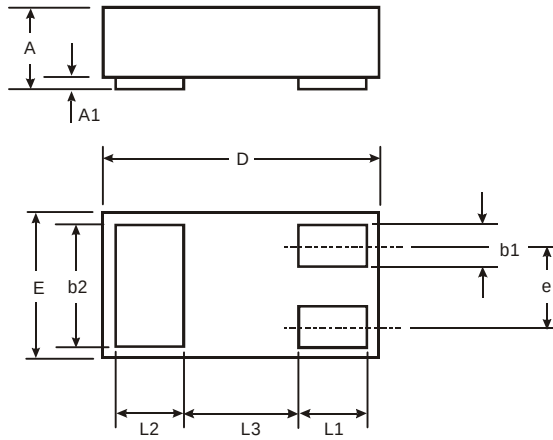


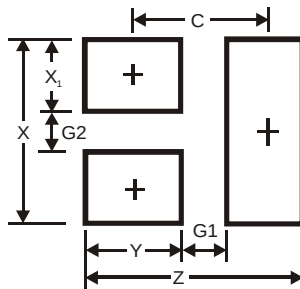
Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions



DFN1006H4-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0	0.05	0.02
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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